



NCE N-Channel Super Trench Power MOSFET

Description

The NCEP85T25 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

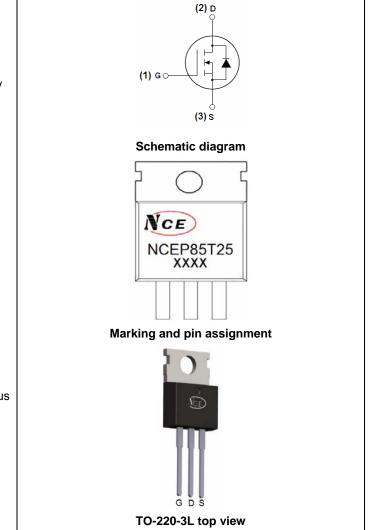
- V_{DS} =85V,I_D =250A
 R_{DS(ON)} <2.6mΩ @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T25	NCEP85T25	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	85	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	250	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	180	A
Pulsed Drain Current	I _{DM}	1000	A
Maximum Power Dissipation	PD	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	2000	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C







Thermal Characteristic

	Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ extsf{ heta}JC}$	0.5	°C/W
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Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	I					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =85V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·		•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I _D =100A	-	2.2	2.6	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =100A	-	90	-	S
Dynamic Characteristics (Note4)	· ·			·		
Input Capacitance	C _{lss}		-	10700	-	PF
Output Capacitance	C _{oss}	V _{DS} =40V,V _{GS} =0V, F=1.0MHz	-	1700	-	PF
Reverse Transfer Capacitance	C _{rss}		-	76	-	PF
Switching Characteristics (Note 4)	· ·		•			
Turn-on Delay Time	t _{d(on)}		-	28	-	nS
Turn-on Rise Time	tr	V _{DD} =40V,I _D =100A	-	73	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_G =1.6 Ω	-	86	-	nS
Turn-Off Fall Time	t _f		-	33	-	nS
Total Gate Charge	Qg	\/	-	142		nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =100A, V _{GS} =10V	-	56		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	24		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _F = I _S	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	250	Α
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	115		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	320		nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ \!\! \mathbb{C}$,V_DD=42.5V,V_G=10V,L=0.5mH,Rg=25\Omega

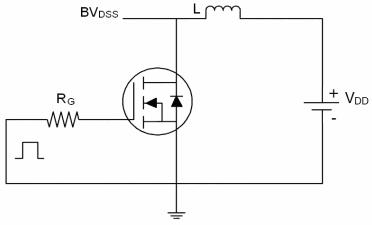


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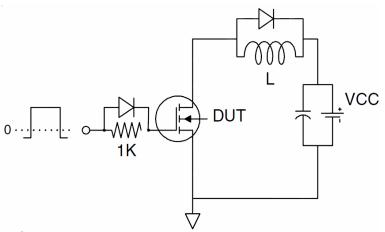




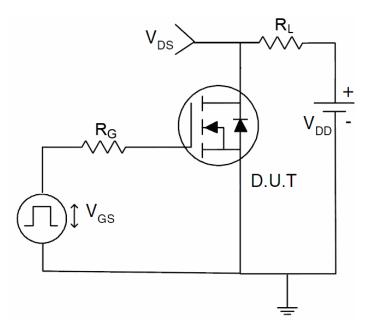
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



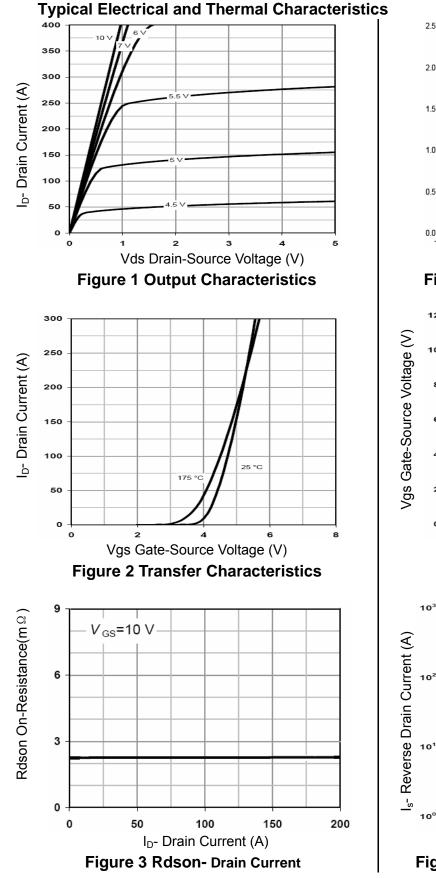
3) Switch Time Test Circuit





NCEP85T25





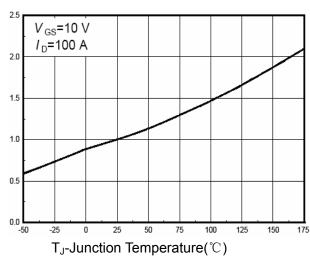
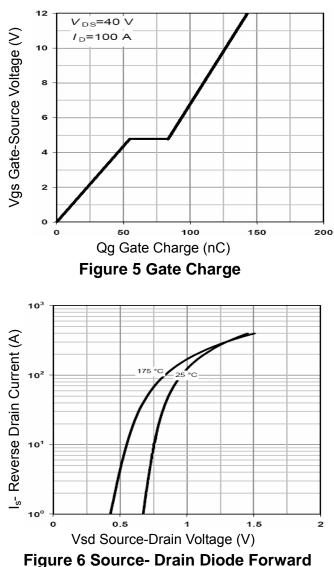


Figure 4 Rdson-JunctionTemperature

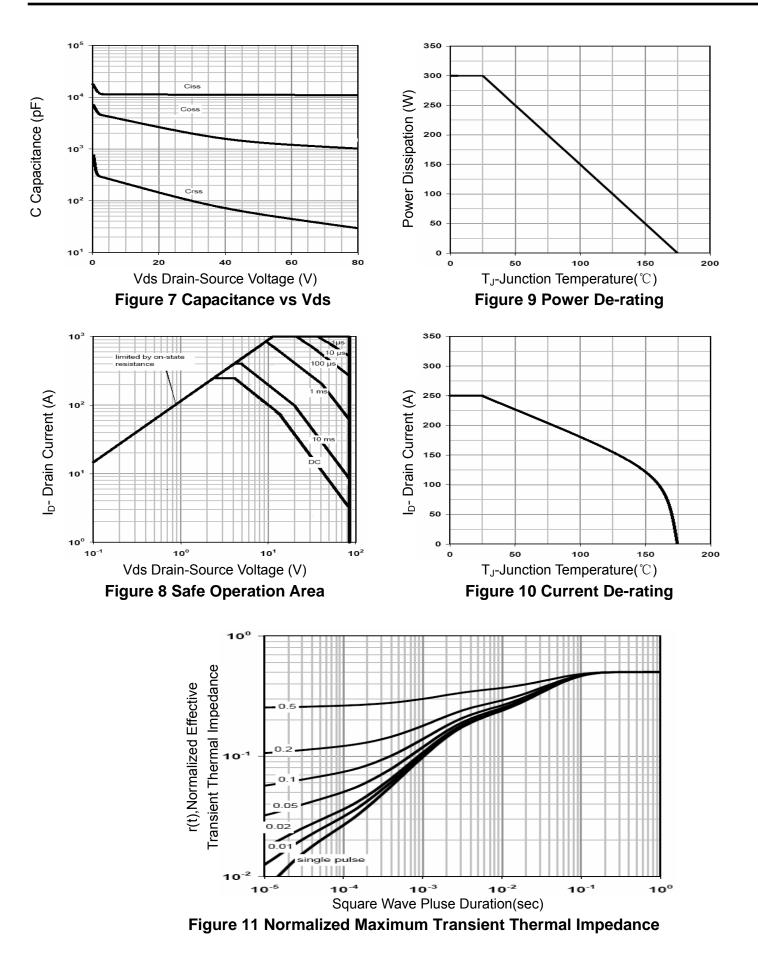




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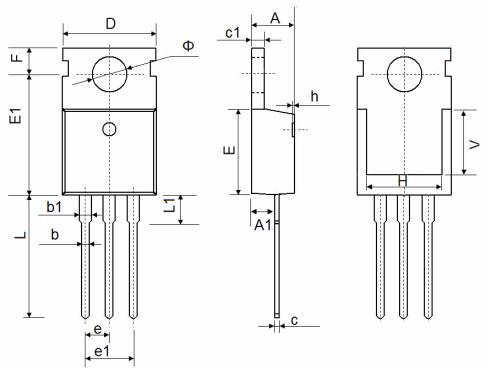


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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
E	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.540	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	7.500 REF.		0.295 REF.			
Φ	3.400	3.800	0.134	0.150		







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